

Abstract**Apparatus and method for depositing a layer of semiconductor material on a substrate wafer**

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An apparatus for depositing a layer of semiconductor material on a substrate wafer, comprising

a base ring between an upper and a lower dome;

a susceptor as carrier of the substrate wafer during the deposition of the layer;

10 a gas inlet and a gas outlet, an outgoing gas line and gas supply lines for passing process gas over an upper side face of the substrate wafer;

a slit valve tunnel and a slit valve door; and

a lifting and rotating means for lifting and turning the susceptor and the substrate wafer,

15 wherein one or more apparatus constituents consisting of stainless steel are covered with an amorphous layer which comprises silicon and hydrogen.

Drawing for the Abstract: fig. 1